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FCX458

400V NPN HIGH VOLTAGE TRANSISTOR IN SOT89

Features

- $BV_{CEO} > 400V$
- $I_C = 225mA$ Continuous Collector Current
- $I_{CM} = 500mA$ Peak Pulse Current
- Excellent h_{FE} Characteristics up to 100mA
- Low saturation voltage $V_{CE(sat)} < 200mV$ @ 20mA
- Complementary PNP Type: FCX558
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

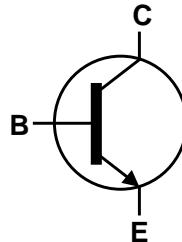
Mechanical Data

- Case: SOT89
- Case Material: Molded Plastic. "Green" Molding Compound.
- UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish - Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.055 grams (Approximate)

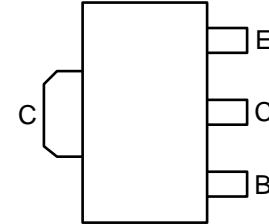
SOT89



Top View



Equivalent Circuit



Top View
Pin-Out

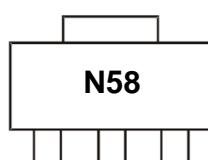
Ordering Information (Note 4)

Product	Compliance	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
FCX458TA	AEC-Q101	N58	7	12mm	1,000

Notes:

1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen and Antimony free, "Green" and Lead-Free.
3. Halogen and Antimony free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
4. For packaging details, go to our website at <http://www.diodes.com/products/packages.html>.

Marking Information



N58 = Product Type Marking Code

Absolute Maximum Ratings (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	400	V
Collector-Emitter Voltage	V_{CEO}	400	V
Emitter-Base Voltage	V_{EBO}	7	V
Continuous Collector Current	I_C	225	mA
Peak Pulse Current	I_{CM}	500	mA
Base Current	I_B	200	mA

Thermal Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Power Dissipation	P_D	0.7	W
		1.0	
		1.5	
		2.0	
Thermal Resistance, Junction to Ambient Air	$R_{\theta JA}$	178	°C/W
		125	
		83	
		60	
Thermal Resistance, Junction to Lead	$R_{\theta JL}$	22	°C
Operating and Storage Temperature Range	T_J, T_{STG}	-65 to +150	

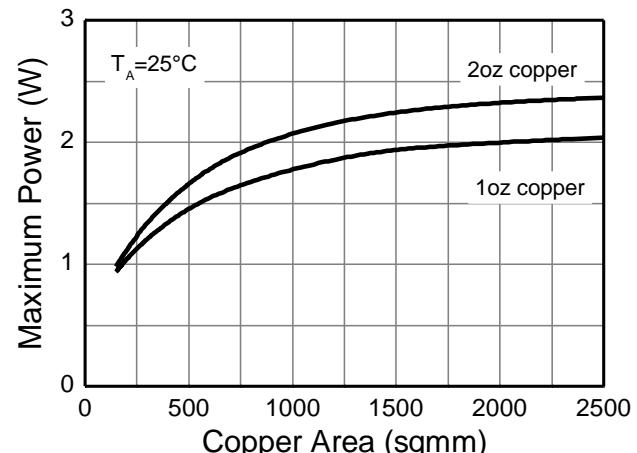
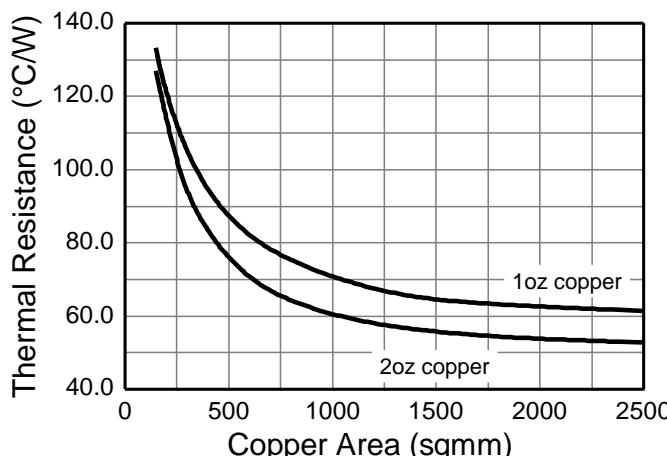
ESD Ratings (Note 10)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	C

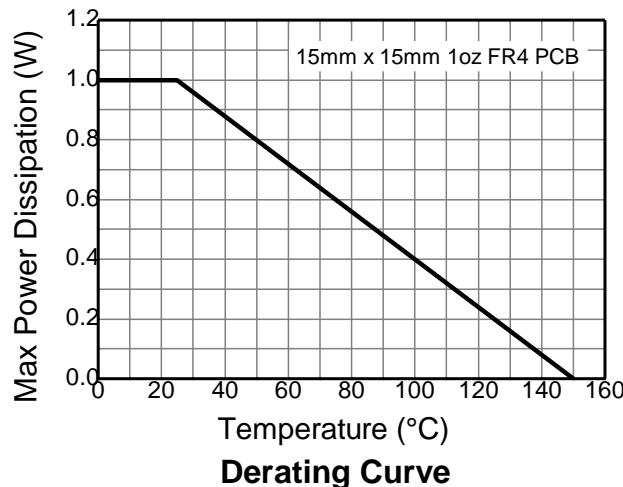
Notes:

5. For a device mounted with the exposed collector pad on minimum recommended pad layout (MRP) 1oz copper that is on a single-sided 1.6mm FR4 PCB; device is measured under still air conditions whilst operating in a steady-state.
6. Same as Note 5, except the device is mounted with the exposed collector pad on 15mm x 15mm 1oz copper.
7. Same as Note 5, except the device is mounted with the exposed collector pad on 25mm x 25mm 1oz copper.
8. Same as Note 5, except the device is mounted with the exposed collector pad on 50mm x 50mm 1oz copper.
9. Thermal resistance from junction to solder-point (on the exposed collector pad).
10. Refer to JEDEC specification JESD22-A114 and JESD22-A115.

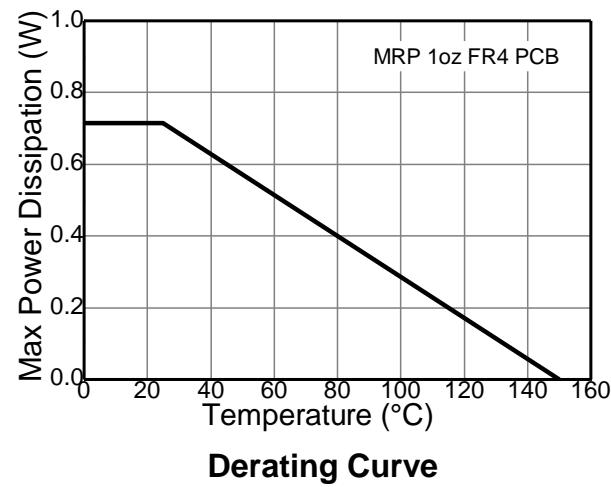
Thermal Characteristics and Derating Information



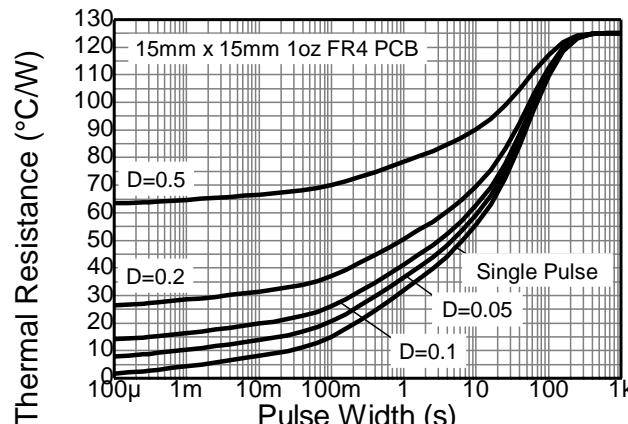
Thermal Characteristics and Derating Information (cont.)



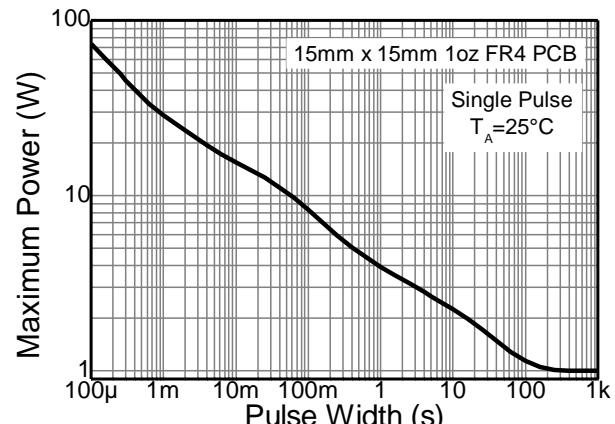
Derating Curve



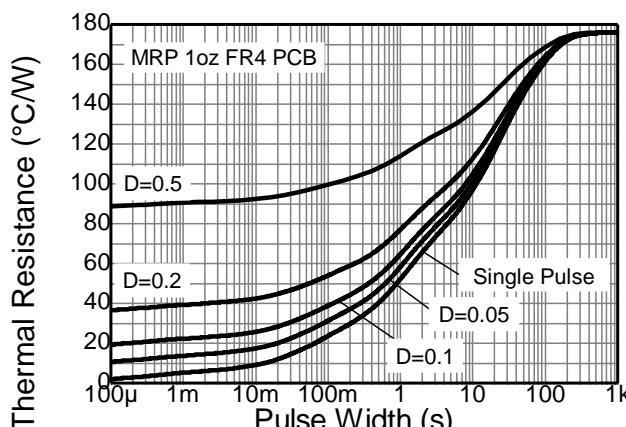
Derating Curve



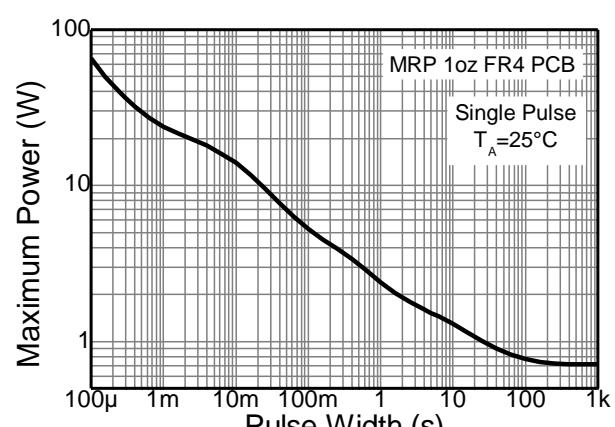
Transient Thermal Impedance



Pulse Power Dissipation



Transient Thermal Impedance



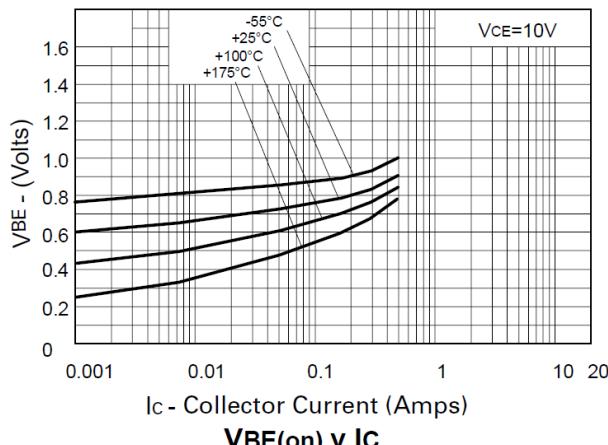
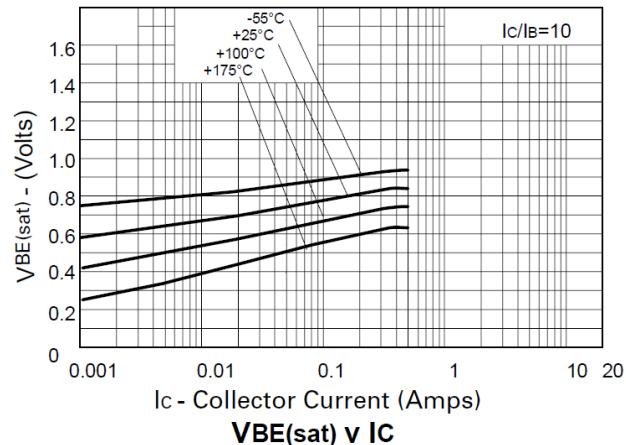
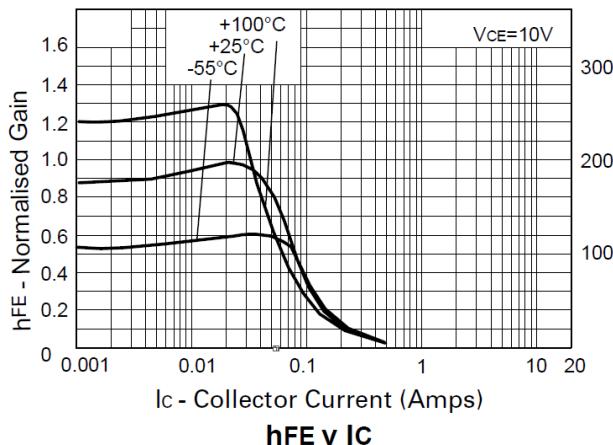
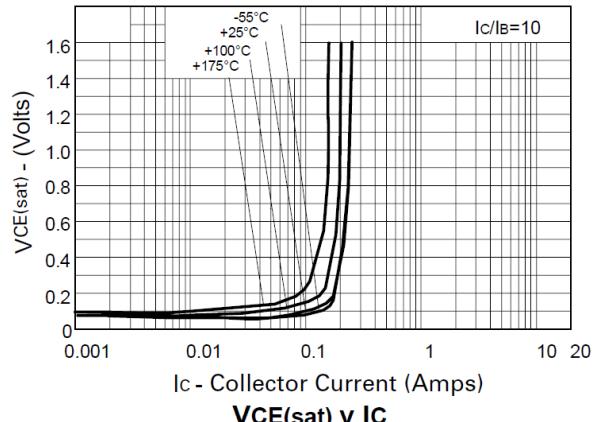
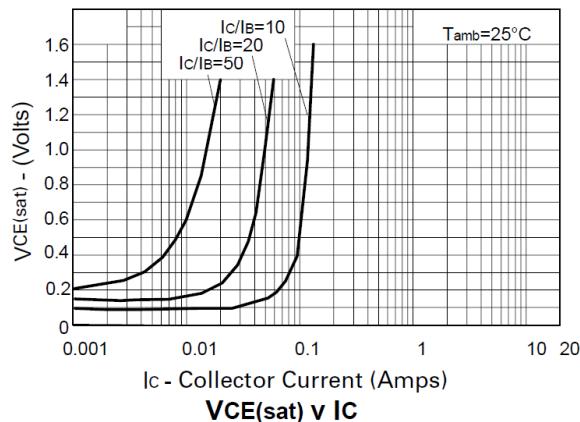
Pulse Power Dissipation

Electrical Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV_{CBO}	400	—	—	V	$I_C = 100\mu\text{A}$
Collector-Emitter Breakdown Voltage (Note 11)	BV_{CEO}	400	—	—	V	$I_C = 1\text{mA}$
Emitter-Base Breakdown Voltage	BV_{EBO}	7	—	—	V	$I_E = 100\mu\text{A}$
Collector-Base Cutoff Current	I_{CBO}	—	<1	100	nA	$V_{\text{CB}} = 320\text{V}$
Collector Cutoff Current	I_{CES}	—	<1	100	nA	$V_{\text{CES}} = 320\text{V}$
Emitter Cutoff Current	I_{EBO}	—	<1	100	nA	$V_{\text{EB}} = 5.6\text{V}$
Collector-Emitter Saturation Voltage (Note 11)	$V_{\text{CE(sat)}}$	—	—	200	mV	$I_C = 20\text{mA}, I_B = 2\text{mA}$
		—	—	500	mV	$I_C = 50\text{mA}, I_B = 6\text{mA}$
Base-Emitter Saturation Voltage (Note 11)	$V_{\text{BE(sat)}}$	—	—	900	mV	$I_C = 50\text{mA}, I_B = 5\text{mA}$
Base-Emitter Turn-On Voltage (Note 11)	$V_{\text{BE(on)}}$	—	—	900	mV	$I_C = 50\text{mA}, V_{\text{CE}} = 10\text{V}$
DC Current Gain (Note 11)	h_{FE}	100 100 15	—	300	—	$I_C = 1\text{mA}, V_{\text{CE}} = 10\text{V}$ $I_C = 50\text{mA}, V_{\text{CE}} = 10\text{V}$ $I_C = 100\text{mA}, V_{\text{CE}} = 10\text{V}$
Transitional Frequency	f_T	50	—	—	MHz	$I_C = 10\text{mA}, V_{\text{CE}} = 20\text{V}, f = 20\text{MHz}$
Output Capacitance	C_{obo}	—	—	5	pF	$V_{\text{CB}} = 20\text{V}, f = 1\text{MHz}$
Turn-On Time	t_{on}	—	135	—	ns	$I_C = 50\text{mA}, V_{\text{CE}} = 100\text{V}$
Turn-Off Time	t_{off}	—	2260	—	ns	$I_{B1} = 5\text{mA}, I_{B2} = -10\text{mA}$

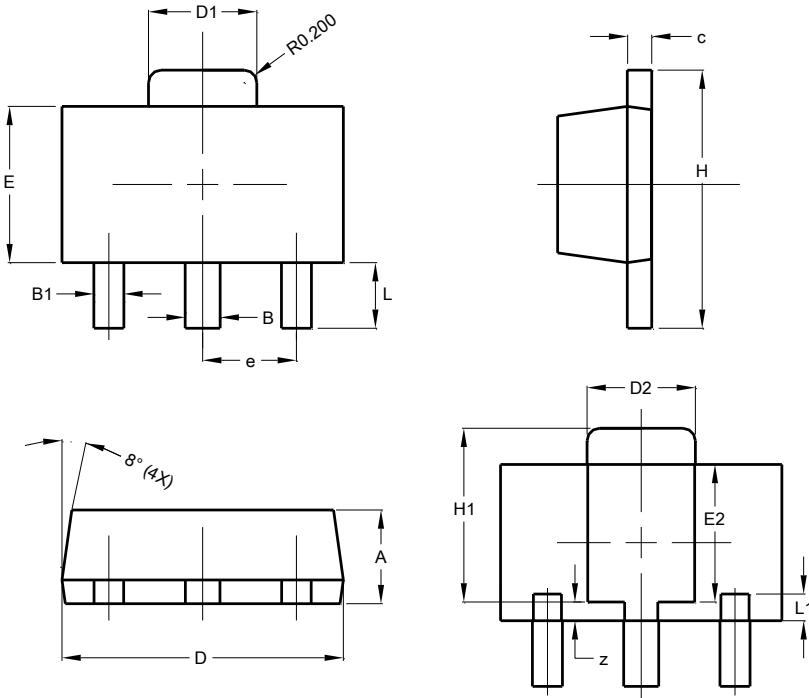
Note: 11. Measured under pulsed conditions. Pulse width $\leq 300\mu\text{s}$. Duty cycle $\leq 2\%$

Typical Electrical Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)



Package Outline Dimensions

Please see AP02002 at <http://www.diodes.com/datasheets/ap02002.pdf> for the latest version.

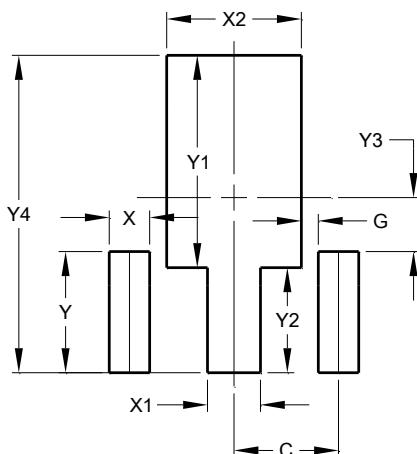


SOT89			
Dim	Min	Max	Typ
A	1.40	1.60	1.50
B	0.50	0.62	0.56
B1	0.42	0.54	0.48
c	0.35	0.43	0.38
D	4.40	4.60	4.50
D1	1.62	1.83	1.733
D2	1.61	1.81	1.71
E	2.40	2.60	2.50
E2	2.05	2.35	2.20
e	-	-	1.50
H	3.95	4.25	4.10
H1	2.63	2.93	2.78
L	0.90	1.20	1.05
L1	0.427 REF		
Z	0.30 REF		

All Dimensions in mm

Suggested Pad Layout

Please see AP02001 at <http://www.diodes.com/datasheets/ap02001.pdf> for the latest version.



Dimensions	Value (in mm)
C	1.500
G	0.244
X	0.580
X1	0.760
X2	1.933
Y	1.730
Y1	3.030
Y2	1.500
Y3	0.770
Y4	4.530

Note: For high voltage applications, the appropriate industry sector guidelines should be considered with regards to creepage and clearance distances between device terminals and PCB tracking.

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